## **AEDS-9300**

Transmissive Photointerrupter

**Data Sheet** 



#### **Description**

The photointerrupter consists of a Gallium Arsenide infrared light emitting diode and a NPN silicon phototransistor built in a black plastic housing. It is a transmissive subminiature photointerrupter.

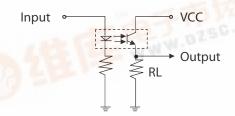


Figure 1: Illustrates Basic Configuration of Photointerrupter

#### **Features**

- Non-Contact Sensing
- Infra-Red Wavelength
- Fast Switching Speed
- Mounting Guide Pins
- **RoHS Compliant**
- -25 °C to +85 °C Operating Temp.

### **Applications**

- **Optical Switch**
- **ATM Machines**

- Edge, Position Detections WWW.0750.GD Office Automation Equipments

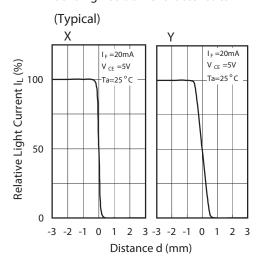


#### **Theory of Operation**

The photo-interrupter consists of an Infrared light source and a photo-diode in a single Dual-in-Line package. The photo-interrupter could be mounted onto a PC board with a current-limiting resistor in series externally with the Infrared Emitting Diode. With this, such input voltage for the emitting diode could share the same voltage level as VCC.

Regarding the photo-interrupter output, there will always be current output measured but with the external resistor, RL connected as shown in Figure 1, analog voltage output could then be obtained.

**Sensing Position Characteristics** 



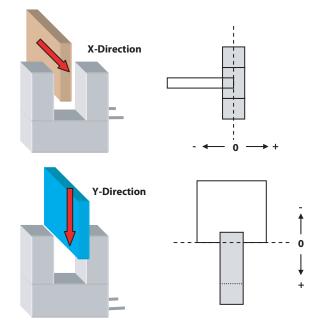


Figure 2: Illustrates Photo-Interrupter Positioning Sensing Characteristics. Obstacles (Slots) could interrupt along X-axis or Y-axis

With both the infrared light source and the photo diode in a single package, the photo-interrupter employs transmissive technology to sense obstacles existence, acts as on / off switchers or even to sense low-resolution rotary or linear motions. The photo-interrupter is specified for operation over -25 °C to +85 °C temperature range.

As a basic switcher, the photo-interrupter would have a position detecting characteristics as shown in Figure 2. These characteristic diagrams give the relationship between Relative Light Current, IL and Distance of displacement, d. Note that the slot (obstacle) introduced in between the emitting diode and the photo-diode could applied in two directions. One is of X-axis and another would be of Y-axis.

Therefore, with the presence of slot, the photo-interrupter would actually give a low logic output. Vice versa, the photo-interrupter will provide a high logic output without the existence of the slot. Refer to Figure 3. Typically, Rise Time, tr and Fall Time tf will have the same value, 15µs.

With special design of the slots, periodic presence and absence could be generated. Such output signal is useful in determining low-resolution (>0.5mm pitch) motor rotation positioning and motor spinning speed.

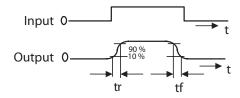


Figure 3: Response Time Measurement of Output Signal.



Figure 4: Periodical Output signal could be used to determine the Motor Spinning Speed and Rotation positioning.

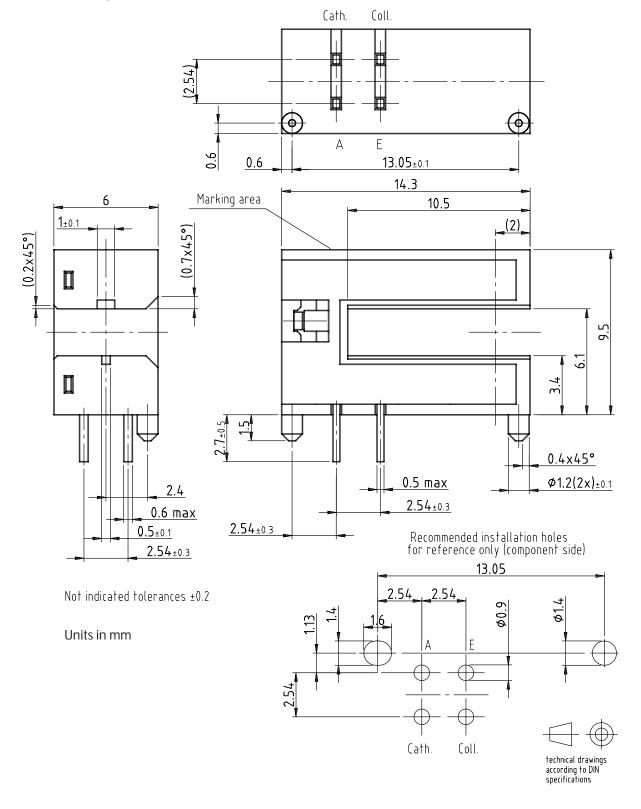
# Absolute Maximum Ratings @ T<sub>A</sub>=25°C

Parameter	Maximum Rating	Unit		
Reverse voltage	5	V		
Forward current	50	mA		
Forward surge current (10µs pulse)	1	A		
Collector Emitter voltage	30	V		
Emitter Collector voltage	5	V		
Power dissipation	175	mW		
Operation temperature range	-25℃ to 85℃			
Storage temperature range	-40°C to 85°C			
Soldering temperature	260°C for 5 seconds			

## Optical-Electrical Characteristics $T_A$ =25°C

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Forward voltage	V <sub>F</sub>	-	1.2	1.35	V	I <sub>F</sub> =20mA
Collector Current	I <sub>C</sub>	8.0	-	10	mA	I <sub>F</sub> =20mA, Vce = 5V
Collector Emitter voltage	$V_{CEO}$	30	-	-	V	I <sub>e</sub> =0.1mA, E <sub>e</sub> =0mW/cm <sup>2</sup>
Emitter Collector voltage	$V_{\text{ECO}}$	5	-	-	V	I <sub>e</sub> =0.1mA, E <sub>e</sub> =0mW/cm <sup>2</sup>
Collector dark current	I <sub>CEO</sub>	-	-	100	nA	V <sub>CE</sub> =10V, E <sub>e</sub> =0mW/cm <sup>2</sup>
Collector Emitter saturation voltage	$V_{CE(SAT)}$	-	-	0.4	V	I <sub>e</sub> =0.5mA, E <sub>e</sub> =0.1mW/cm <sup>2</sup>
Rising time	T <sub>r</sub>	-	15	-	μs	$V_{CE}$ =5V, $R_L$ =1k $\Omega$ , $I_C$ =1mA
Falling time	T <sub>f</sub>	-	15	-	μs	_

## **Outline Drawing**



### **Typical Optical-Electrical Curves**

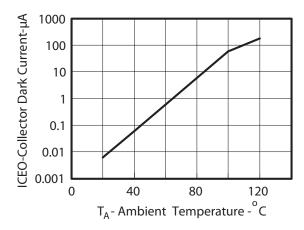


Figure 5: Collector Dark Current Vs Ambient Temperature

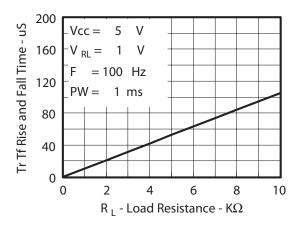


Figure 7: Rise and Fall Times Vs Load Resistance

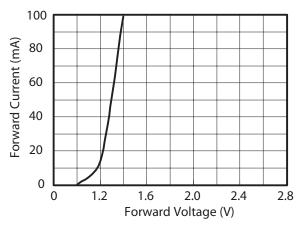


Figure 9: Forward Current Vs Forward Voltage

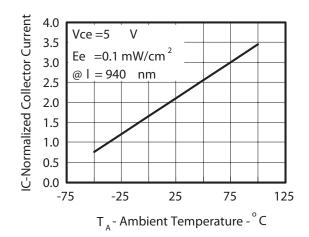


Figure 6: Normalized Collector Current Vs Ambient Temperature

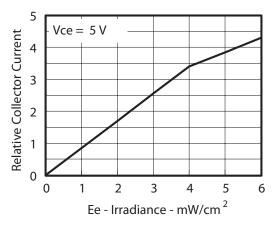


Figure 8: Relative Collector Current Vs Irradiance

